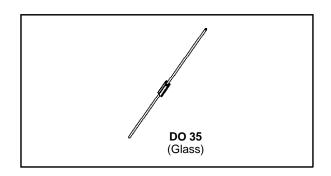


# SMALL SIGNAL SCHOTTKY DIODE

#### **DESCRIPTION**

Metal to silicon junction diode featuring high breakdown, low turn-on voltage and ultrafast switching. Primarly intended for high level UHF/VHF detection and pulse application with broad dynamic range. Matched batches are available on request.



## **ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter	Value	Unit	
$V_{RRM}$	Repetitive Peak Reverse Voltage	70	V	
l <sub>F</sub>	Forward Continuous Current*	15	mA	
P <sub>tot</sub>	Power Dissipation*	T <sub>a</sub> = 25°C	430	mW
T <sub>stg</sub> Tj	Storage and Junction Temperature Range	- 65 to 200 - 65 to 200	°C	
TL	Maximum Lead Temperature for Soldering during from Case	230	°C	

## THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R <sub>th(j-a)</sub>	Junction-ambient*	400	°C/W

#### **ELECTRICAL CHARACTERISTICS**

## STATIC CHARACTERISTICS

Symbol		Min.	Тур.	Max.	Unit		
$V_{BR}$	T <sub>amb</sub> = 25°C	$I_R = 10\mu A$		70			٧
V <sub>F</sub> * *	T <sub>amb</sub> = 25°C	I <sub>F</sub> = 1mA				0.41	V
	T <sub>amb</sub> = 25°C	I <sub>F</sub> = 15mA				1	
I <sub>R</sub> * *	T <sub>amb</sub> = 25°C	V <sub>R</sub> = 50V				0.2	μА

### DYNAMIC CHARACTERISTICS

	Symbol	Test Conditions				Тур.	Max.	Unit
ĺ	С	T <sub>amb</sub> = 25°C	$V_R = 0V$	f = 1MHz			2	pF
	τ	T <sub>amb</sub> = 25°C	$I_F = 5mA$	Krakauer Method			100	ps

<sup>\*</sup> On infinite heatsink with 4mm lead length

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<sup>\*\*</sup> Pulse test:  $t_p \le 300 \mu s \ \delta < 2\%$ .

Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.

Figure 1. Forward current versus forward voltage at low level (typical values).

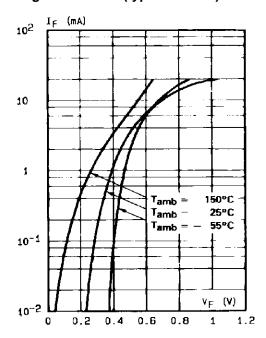


Figure 2. Capacitance C versus reverse applied voltage  $V_{\mbox{\scriptsize R}}$  (typical values).

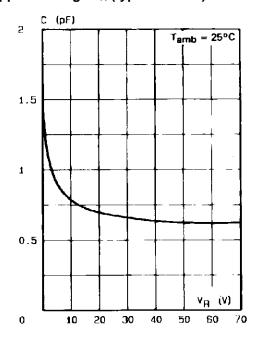


Figure 3. Reverse current versus ambient temperature.

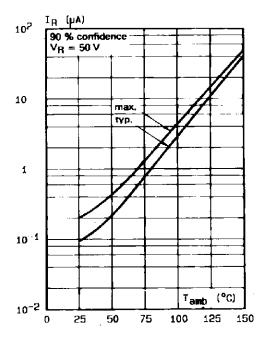
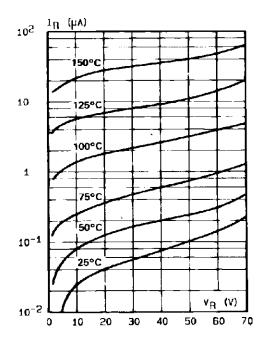
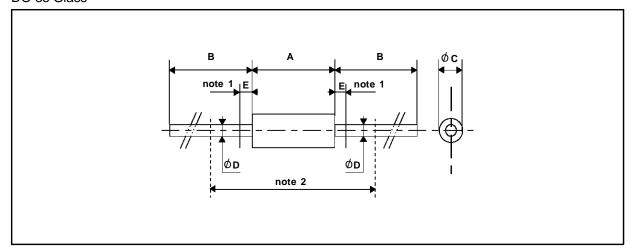


Figure 4. Reverse current versus continuous reverse voltage (typical values).



### **PACKAGE MECHANICAL DATA**

#### DO 35 Glass



	DIMENSIONS			NOTES		
REF.	REF. Millimeters		Inches			
	Min.	Max.	Min.	Max.		
Α	3.050	4.500	0.120	0.117	1 - The lead diameter Ø D is not controlled over zone E	
В	12.7		0.500			
ØC	1.530	2.000	0.060	0.079	2 - The minimum axial lengh within which the device may be placed with its leads bent at right angles is 0.59"(15 mm)	
ØD	0.458	0.558	0.018	0.022	placed with its leads bent at right angles is 0.59 (15 min)	
Е		1.27		0.050		

Cooling method: by convection and conduction Marking: clear, ring at cathode end. Weight: 0.15g

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